

DATA SHEET

NEC

NPN SILICON RF TWIN TRANSISTOR

μPA862TS

NPN SILICON RF TRANSISTOR (WITH 2 DIFFERENT ELEMENTS) IN A 6-PIN SUPER LEAD-LESS MINIMOLD

FEATURES

- Low voltage operation
- 2 different built-in transistors (2SC5435, 2SC5800)
 - Q1: Built-in high gain transistor
 $f_T = 12.0 \text{ GHz TYP.}$, $|S_{21e}|^2 = 11.0 \text{ dB TYP. @ } V_{CE} = 3 \text{ V, } I_C = 10 \text{ mA, } f = 2 \text{ GHz}$
 - Q2: Built-in low phase distortion transistor suited for OSC applications
 $f_T = 4.5 \text{ GHz TYP.}$, $|S_{21e}|^2 = 4.0 \text{ dB TYP. @ } V_{CE} = 1 \text{ V, } I_C = 5 \text{ mA, } f = 2 \text{ GHz}$
- 6-pin super lead-less minimold package

BUILT-IN TRANSISTORS

	Q1	Q2
Flat-lead 3-pin thin-type ultra super minimold part No.	2SC5435	2SC5800

ORDERING INFORMATION

Part Number	Quantity	Supplying Form
μPA862TS	50 pcs (Non reel)	• 8 mm wide embossed taping
μPA862TS-T3	10 kpcs/reel	• Pin 1 (Q1 Collector), Pin 6 (Q1 Base) face the perforation side of the tape

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 50 pcs.

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings		Unit
		Q1	Q2	
Collector to Base Voltage	V _{CBO}	9	9	V
Collector to Emitter Voltage	V _{CEO}	6	5.5	V
Emitter to Base Voltage	V _{EBO}	2	1.5	V
Collector Current	I _C	30	100	mA
Total Power Dissipation	P _{tot} ^{Note}	110 in 1 element		mW
		130 in 2 elements		
Junction Temperature	T _j	150		°C
Storage Temperature	T _{stg}	−65 to +150		°C

Note Mounted on $1.08\text{ cm}^2 \times 1.0\text{ mm}$ (t) glass epoxy PCB

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

(1) Q1

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0 mA	–	–	100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0 mA	–	–	100	nA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 3 V, I _C = 10 mA	75	110	150	–
Gain Bandwidth Product	f _T	V _{CE} = 3 V, I _C = 10 mA, f = 2 GHz	10.0	12.0	–	GHz
Insertion Power Gain	S _{21e} ²	V _{CE} = 3 V, I _C = 10 mA, f = 2 GHz	7.0	11.0	–	dB
Noise Figure	NF	V _{CE} = 3 V, I _C = 3 mA, f = 2 GHz, Z _S = Z _{opt}	–	1.5	2.5	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 3 V, I _E = 0 mA, f = 1 MHz	–	0.4	0.7	pF

(2) Q2

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0 mA	–	–	600	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0 mA	–	–	600	nA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 1 V, I _C = 5 mA	100	120	145	–
Gain Bandwidth Product (1)	f _T	V _{CE} = 1 V, I _C = 5 mA, f = 2 GHz	3.0	4.5	–	GHz
Gain Bandwidth Product (2)	f _T	V _{CE} = 1 V, I _C = 15 mA, f = 2 GHz	5.0	6.5	–	GHz
Insertion Power Gain (1)	S _{21e} ²	V _{CE} = 1 V, I _C = 5 mA, f = 2 GHz	3.0	4.0	–	dB
Insertion Power Gain (2)	S _{21e} ²	V _{CE} = 1 V, I _C = 15 mA, f = 2 GHz	4.5	5.5	–	dB
Noise Figure	NF	V _{CE} = 1 V, I _C = 10 mA, f = 2 GHz, Z _S = Z _{opt}	–	1.9	2.5	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 0.5 V, I _E = 0 mA, f = 1 MHz	–	0.6	0.8	pF

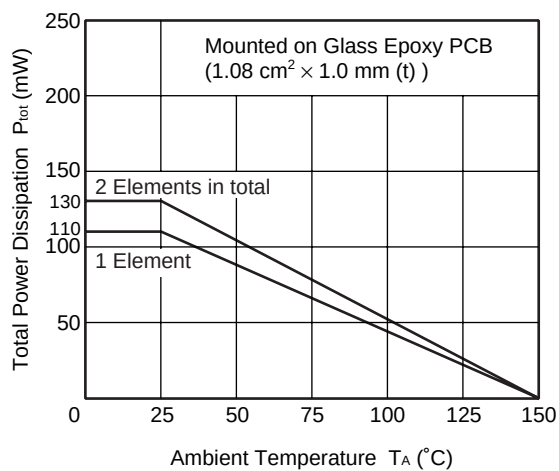
- Notes** 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%
2. Collector to base capacitance when the emitter grounded

h_{FE} CLASSIFICATION

Rank	FB
Marking	vY
h _{FE} Value of Q1	75 to 150
h _{FE} Value of Q2	100 to 145

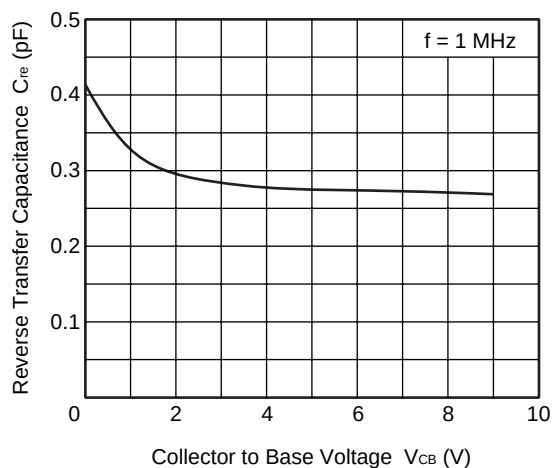
★ TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

TOTAL POWER DISSIPATION
vs. AMBIENT TEMPERATURE



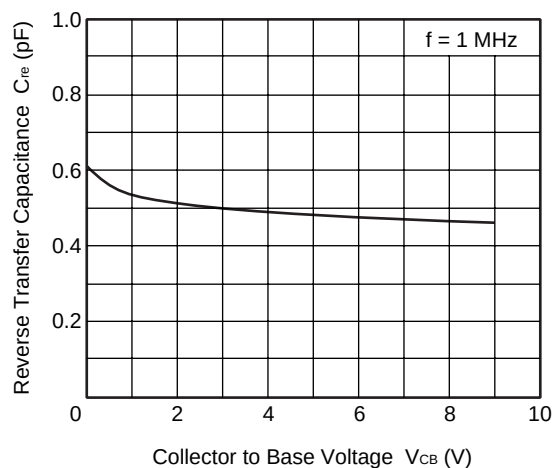
Q1

REVERSE TRANSFER CAPACITANCE
vs. COLLECTOR TO BASE VOLTAGE



Q2

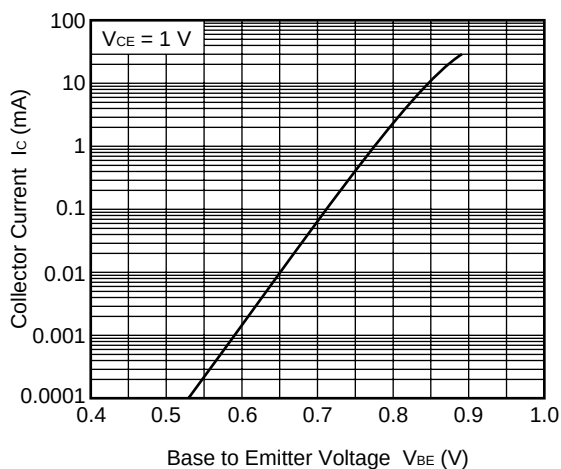
REVERSE TRANSFER CAPACITANCE
vs. COLLECTOR TO BASE VOLTAGE



Remark The graphs indicate nominal characteristics.

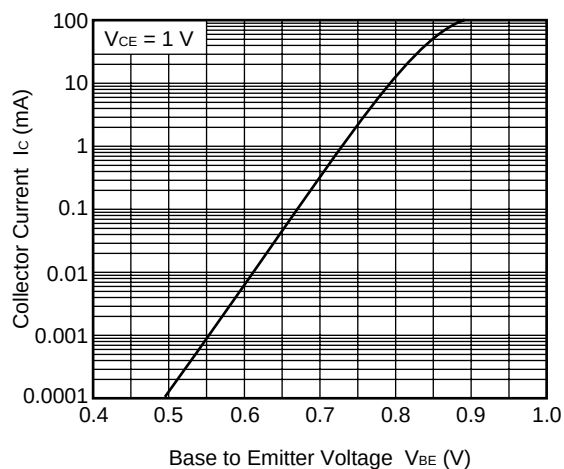
Q1

COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE

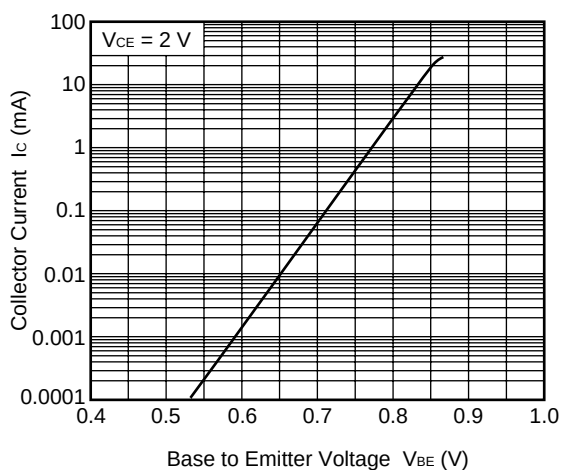


Q2

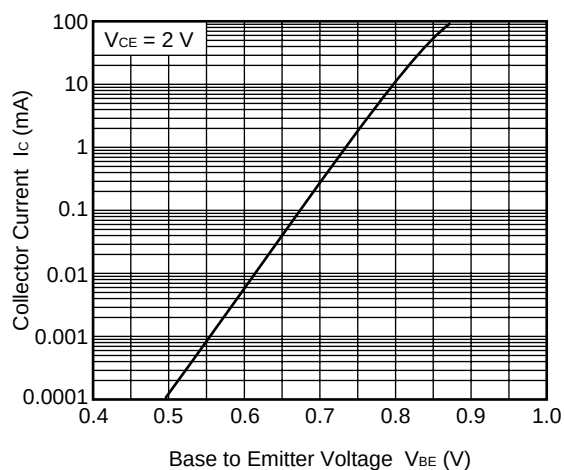
COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



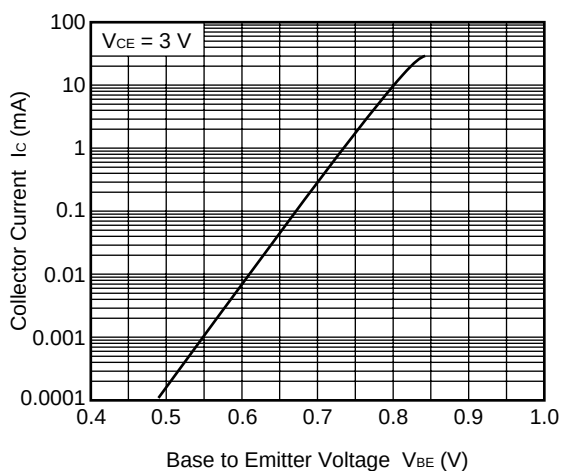
COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs.
BASE TO EMITTER VOLTAGE



Remark The graphs indicate nominal characteristics.